

HiPerFET™ Power MOSFETs IXFL 34N100

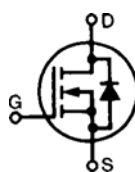
ISOPLUS264™

(Electrically Isolated Backside)

$V_{DSS} = 1000\text{ V}$
 $I_{D25} = 30\text{ A}$
 $R_{DS(on)} = 0.28\ \Omega$

Single Die MOSFET

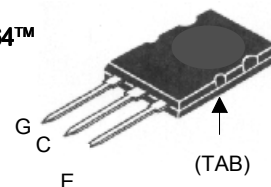
N-Channel Enhancement Mode
 Avalanche Rated, High dv/dt, Low t_{rr}



Preliminary Data Sheet

| Symbol | Test Conditions | Maximum Ratings | |
|------------|---|-----------------|------------------|
| V_{DSS} | $T_J = 25^\circ\text{C}$ to 150°C | 1000 | V |
| V_{DGR} | $T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$ | 1000 | V |
| V_{GS} | Continuous | ± 20 | V |
| V_{GSM} | Transient | ± 30 | V |
| I_{D25} | $T_C = 25^\circ\text{C}$ | 30 | A |
| I_{DM} | $T_C = 25^\circ\text{C}$, Note 1 | 136 | A |
| I_{AR} | $T_C = 25^\circ\text{C}$ | 34 | A |
| E_{AR} | $T_C = 25^\circ\text{C}$ | 64 | mJ |
| E_{AS} | $T_C = 25^\circ\text{C}$ | 4 | J |
| dv/dt | $I_S \leq I_{DM}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$, $R_G = 2\ \Omega$ | 5 | V/ns |
| P_D | $T_C = 25^\circ\text{C}$ | 550 | W |
| T_J | | -55 ... +150 | $^\circ\text{C}$ |
| T_{JM} | | 150 | $^\circ\text{C}$ |
| T_{stg} | | -55 ... +150 | $^\circ\text{C}$ |
| T_L | 1.6 mm (0.063 in.) from case for 10 s | 300 | $^\circ\text{C}$ |
| V_{ISOL} | 50/60 Hz, RMS $t = 1\text{ min}$ $I_{ISOL} \leq 1\text{ mA}$ $t = 1\text{ s}$ | 2500 3000 | V~ V~ |
| Weight | | 5 | g |

ISOPLUS-264™



G = Gate C = Collector
 E = Emitter Tab = Collector

Features

- Silicon chip on Direct-Copper-Bond substrate
 - High power dissipation
 - Isolated mounting surface
 - 2500V electrical isolation
- Low drain to tab capacitance (<30pF)
- Low $R_{DS(on)}$ HDMOST™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control

Advantages

- Easy assembly
- Space savings
- High power density

| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | | |
|--------------|--|---|------|---------------------------|
| | | min. | typ. | max. |
| V_{DSS} | $V_{GS} = 0\text{ V}$, $I_D = 3\text{ mA}$ | 1000 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 8\text{ mA}$ | 2.5 | | 5.0 V |
| I_{GSS} | $V_{GS} = \pm 20\text{ V}_{DC}$, $V_{DS} = 0$ | | | $\pm 100\text{ nA}$ |
| I_{DSS} | $V_{DS} = V_{DSS}$, $V_{GS} = 0\text{ V}$ | | | 100 μA 2 mA |
| $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$, $I_D = I_T$ Note 1 | | | 0.28 Ω |

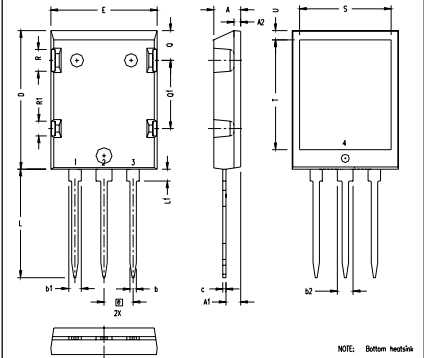
| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | Characteristic Values | | |
|--------------|---|---|-----------------------|-------|------|
| | | | min. | typ. | max. |
| g_{fs} | $V_{DS} = 15\text{ V}; I_D = I_T$ | Note 2 | 18 | 40 | S |
| C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$ | | | 9200 | pF |
| C_{oss} | | | | 1200 | pF |
| C_{rss} | | | | 300 | pF |
| $t_{d(on)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$ $R_G = 1\ \Omega$ (External) | | | 41 | ns |
| t_r | | | | 65 | ns |
| $t_{d(off)}$ | | | | 110 | ns |
| t_f | | | | 30 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$ | | | 380 | nC |
| Q_{gs} | | | | 65 | nC |
| Q_{gd} | | | | 185 | nC |
| R_{thJC} | | | | 0.225 | K/W |
| R_{thCK} | | | 0.05 | | K/W |

Source-Drain Diode

| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | Characteristic Values | | |
|----------|--|---|-----------------------|------|---------------|
| | | | min. | typ. | max. |
| I_S | $V_{GS} = 0\text{ V}$ | | | 34 | A |
| I_{SM} | Repetitive; pulse width limited by T_{JM} | | | 136 | A |
| V_{SD} | $I_F = I_S, V_{GS} = 0\text{ V}$, Note 1 | | | 1.3 | V |
| t_{rr} | $I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$ | $T_J = 25^\circ\text{C}$ | 180 | | ns |
| Q_{RM} | | $T_J = 125^\circ\text{C}$ | 330 | | ns |
| | | $T_J = 25^\circ\text{C}$ | 2 | | μC |
| I_{RM} | | | 8 | | A |

- Note: 1. Pulse width limited by T_{JM}
 2. Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$
 3. Test current $I_T = 30\text{ A}$

ISOPLUS 264 OUTLINE



| SYM | INCHES | | MILLIMETERS | |
|-----|----------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .190 | .205 | 4.83 | 5.21 |
| A1 | .102 | .118 | 2.59 | 3.00 |
| A2 | .046 | .055 | 1.17 | 1.40 |
| b | .045 | .055 | 1.14 | 1.40 |
| b1 | .087 | .102 | 2.21 | 2.59 |
| b2 | .111 | .126 | 2.82 | 3.20 |
| c | .020 | .029 | 0.51 | 0.74 |
| D | 1.020 | 1.040 | 25.91 | 26.42 |
| E | .770 | .799 | 19.56 | 20.29 |
| e | .215 BSC | | 5.46 BSC | |
| L | .780 | .820 | 19.81 | 20.83 |
| L1 | .080 | .102 | 2.03 | 2.59 |
| Q | .210 | .235 | 5.33 | 5.97 |
| Q1 | .490 | .513 | 12.45 | 13.03 |
| R | .150 | .180 | 3.81 | 4.57 |
| R1 | .100 | .130 | 2.54 | 3.30 |
| S | .668 | .690 | 16.97 | 17.53 |
| T | .801 | .821 | 20.34 | 20.85 |
| U | .065 | .080 | 1.65 | 2.03 |

NOTE: Bottom heatsink meets 2500Vrms isolation to the other pins.